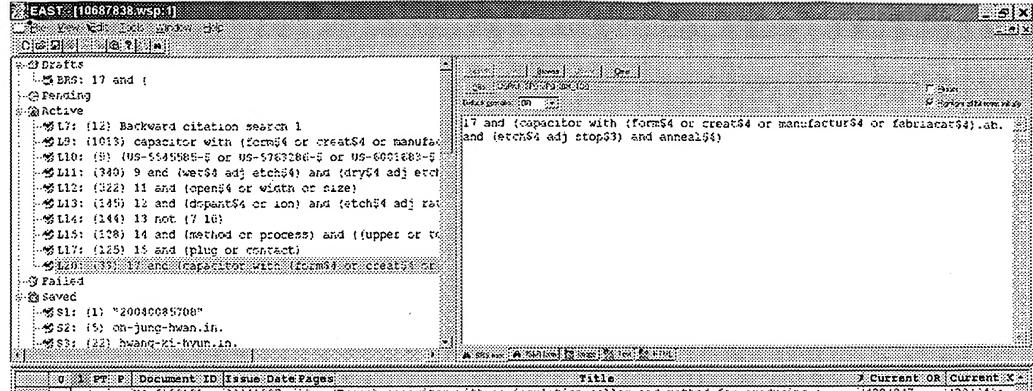
Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	12	("20010012688"   "20020027288"   "5330614"   "5545585"   "5631185"   "5763306"   "5933724"   "6001683"   "6194309"   "6215187"   "6228762"   "6239022").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/14 14:49
L9	1013	capacitor with (form\$4 or creat\$4 or manufactur\$4 or fabriacat\$4) and (etch\$4 adj stop\$3) and anneal\$4	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/02/14 14:58
L10	9	(US-5545585-\$ or US-5763286-\$ or US-6001683-\$ or US-6215187-\$ or US-6548853-\$ or US-6566188-\$ or US-6586312-\$ or US-6682984-\$ or US-6759704-\$).did.	USPAT	OR	OFF	2005/02/14 14:52
L11	340	9 and (wet\$4 adj etch\$4) and (dry\$4 adj etch\$4)	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/02/14 14:53
L12	322	11 and (open\$4 or width or size)	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/02/14 14:54
L13	145	12 and (dopant\$4 or ion) and (etch\$4 adj rate)	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/02/14 14:55
L14	144	13 not (7 10)	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/02/14 14:55
L15	128	14 and (method or process) and ((upper or top or first or second) adj3 layer)	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/02/14 14:56
L17	125	15 and (plug or contact)	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/02/14 14:57
L20	39	17 and (capacitor with (form\$4 or creat\$4 or manufactur\$4 or fabriacat\$4).ab. and (etch\$4 adj stop\$3) and anneal\$4)	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/02/14 15:00
<b>S1</b>	1	"20040085708"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 18:21
S2	5	oh-jung-hwan.in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:20
S3	22	hwang-ki-hyun.in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:20
S4	17	park-jae-young.in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:20
S5	31	hwang-in-seak.in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:20
S6	85	park-young-wook.in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:20
<b>S</b> 7	2	"6700153"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:22

58	67	(oh-jung-hwan.in. hwang-ki-hyun.in. park-jae-young.in. hwang-in-seak.in. park-young-wook.in.) and (capacitor with (electrode or plate))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:31
59	14	((oh-jung-hwan.in. hwang-ki-hyun.in. park-jae-young.in. hwang-in-seak.in. park-young-wook.in.) and (capacitor with (electrode or plate))) and (etch\$4 with rate)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:32
<b>S10</b>	10	(((oh-jung-hwan.in. hwang-ki-hyun.in. park-jae-young.in. hwang-in-seak.in. park-young-wook.in.) and (capacitor with (electrode or plate))) and (etch\$4 with rate)) and plug	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:23
S11	6	((((oh-jung-hwan.in. hwang-ki-hyun.in. park-jae-young.in. hwang-in-seak.in. park-young-wook.in.) and (capacitor with (electrode or plate))) and (etch\$4 with rate)) and plug) and (etch adj stop\$)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:32
S12	17	(("0018248" "0019107" "0028553" "0034114" "5100825" "54348 12" "5468684" "5545585" "5763286" "5885865" "5943581" "000 0596" "6022772" "6168987" "6215187" "6222722" "6258689" "6 268244" "6271084" "6312986" "6586312" "6682984").PN.) and (capacitor with (electrode or plate))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:32
S13	7	((("0018248" "0019107" "0028553" "0034114" "5100825" "5434 812" "5468684" "5545585" "5763286" "5885865" "5943581" "00 00596" "6022772" "6168987" "6215187" "6222722" "6258689" " 6268244" "6271084" "6312986" "6586312" "6682984").PN.) and (capacitor with (electrode or plate))) and (etch adj stop\$)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:32
S14	2	(((("0018248" "0019107" "0028553" "0034114" "5100825" "543 4812" "5468684" "5545585" "5763286" "5885865" "5943581" "0 000596" "6022772" "6168987" "6215187" "6222722" "6258689"  "6268244" "6271084" "6312986" "6586312" "6682984").PN.) and (capacitor with (electrode or plate))) and (etch adj stop\$)) and (etch\$4 with rate)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:37
S15	4	("5053351"   "5164881"   "5185282"   "5403767").PN.	USPAT	OR	ON	2004/07/26 19:36
S16	5	(((("0018248" "0019107" "0028553" "0034114" "5100825" "543 4812" "5468684" "5545585" "5763286" "5885865" "5943581" "0 000596" "6022772" "6168987" "6215187" "6222722" "6258689"  "6268244" "6271084" "6312986" "6586312" "6682984").PN.) and (capacitor with (electrode or plate))) and (etch adj stop\$)) not ((((("0018248" "0019107" "0028553" "0034114" "5100825" "54 34812" "5468684" "5545585" "5763286" "5885865" "5943581" " 0000596" "6022772" "6168987" "6215187" "6222722" "6258689 " "6268244" "6271084" "6312986" "6586312" "6682984").PN.)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:48
		and (capacitor with (electrode or plate))) and (etch adj stop\$)) and (etch\$4 with rate))				
S17	5	("5656536"   "5770499"   "5851898"   "5869367"   "5891772"). PN.	USPAT	OR	ON	2004/07/26 19:42
S18	10	((("0018248" "0019107" "0028553" "0034114" "5100825" "5434812" "5468684" "5545585" "5763286" "5885865" "5943581" "000596" "6022772" "6168987" "6215187" "6222722" "6258689" "6268244" "6271084" "6312986" "6586312" "6682984").PN.) and (capacitor with (electrode or plate))) not ((("0018248" "0019107" "0028553" "0034114" "5100825" "5434812" "5468684" "5545585" "5763286" "5885865" "5943581" "000596" "6022772" "6168987" "6215187" "6222722" "6258689" "6268244" "6271084" "6312986" "6586312" "6682984").PN.) and (capacitor with (electrode or plate))) and (etch adj stop\$))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/26 19:48
S19	4	("5597756"   "5658818"   "5936308"   "6031293").PN.	USPAT	OR	ON	2004/07/27 10:11
S20	4	"6215187".URPN.	USPAT	OR	ON	2004/07/27 10:11
521	8	("5330614"   "5545585"   "5631185"   "6001683"   "6194309"   "6215187"   "6228762"   "6239022"   "2001/0012688"   "2002/0027288").PN.	USPAT	OR	ON	2004/07/27 10:12
522	0	"6528368".URPN.	USPAT	OR	ON	2004/07/27 10:14
S23	0	"6528368".URPN.	USPAT	OR	ON	2004/07/27 10:14

S24	16	((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.) not ((("5597756"   "5658818"   "5936308"   "6031293").PN.) "6215187".URPN. (("5330614"   "5545585"   "5631185"   "6001683"   "6194309"   "6215187"   "6228762"   "6239022"   "2001/0012688"   "2002/0027288").PN.))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 11:14
S25	144	((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 13:30
526	16	(((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 13:30
S27	13	((((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.) not ((("5597756"   "5658818"   "5936308"   "6031293").PN.) "6215187".URPN. (("5330614"   "5545585"   "5631185"   "6001683"   "6194309"   "6215187"   "6228762"   "6239022"   "2001/0012688"   "2002/0027288").PN.))) and (dry adj etch\$4)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 13:30
S28	3	((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.) not (((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.) not ((("5597756"   "5658818"   "5936308"   "6031293").PN.) "6215187".URPN. (("5330614"   "5545585"   "5631185"   "6001683"   "6194309"   "6215187"   "6228762"   "6239022"   "2001/0012688"   "2002/0027288").PN.))) and (dry adj etch\$4))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 13:31
S29	128	(((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) not ((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 13:31
S30	<sub>,</sub> 27	((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) not ((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.)) and ((etch adj stop) with expose)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 13:31
S31	38	((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) not ((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.)) and ((etch adj stop) with expose\$3)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 13:31
S32	38	(((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) not ((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.)) and ((etch adj stop) with expose\$3)) and (plug)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 16:31
S33	137	oh-jung-hwan.in. hwang-ki-hyun.in. park-jae-young.in. hwang-in-seak.in. park-young-wook.in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 16:32
S34	22	("0018248" "0019107" "0028553" "0034114" "5100825" "54348 12" "5468684" "5545585" "5763286" "5885865" "5943581" "000 0596" "6022772" "6168987" "6215187" "6222722" "6258689" "6 268244" "6271084" "6312986" "6586312" "6682984").PN.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 16:32

S35	33	(((((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) not ((((farbricat\$4 or form\$4 or creat\$4) near2 capacitor) and opening and (wet adj etching) and (etch adj stop) and plug) and ((farbricat\$4 or form\$4 or creat\$4) near2 capacitor).ti.)) and ((etch adj stop) with expose\$3)) and (plug)) not ((oh-jung-hwan. in. hwang-ki-hyun.in. park-jae-young.in. hwang-in-seak.in. park-young-wook.in.) (("0018248" "0019107" "0028553" "0034114" "5100825" "54348 12" "5468684" "5545585" "5763286" "5885865" "5943581" "000 0596" "6022772" "6168987" "6215187" "6222722" "6258689" "6 268244" "6271084" "6312986" "6586312" "6682984").PN.))\	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 16:32
S36	17	"6136643"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/07/27 19:36



	0	<b>. L</b> .:	PT	P	Dt	cument ID	Issue Date	Pages	Title	Current OR	Current X -
	<u></u>	~	г	-	US	6929191	20041207	25	Trench capacitor with an insulation collar and method for producing a		438/2431
100000000000000000000000000000000000000					E 4.				trench capacitor		338/2447
	€.	<b>F</b>	r	-	US	6)98065	20040928	63	Semiconductor memory device hering large storage capacity and minimal step	257/236	25?/30:#
							:		height between memory cell and meripheral circuits		257/3081
	3.3	3".	€.	1	55	6701134	20040914	63	Semiconductor memory device and manufacturing method thereof		257/304; 257/311
		. :			n.		20046810	 36	Mathod of forming an Feram capacitor having a mottom electrode diffusion		257/EZ1.0
	7	۳.	٢	~	U A U A	6773930	20040010	•	parties	: : 4 207 2	
		• • • • •		•••••	D.A. 114	6768916	20040622	e,	Next Act. Method of manufacturing semiconductor integrated circuit devices having a	1438/253	257/E21.50
	€.	Γ.	T.	· •	P.2	6753219	200000000		memory device with a reduced bit line stray capacity and such remiconducto	•	
6	•••	:	,	•••	อีร์.	6674081	20040106		Infrared detecting element, infrared two-dimensional image sensor, and	250/338.2	000
		: .			87.				rethod of panufacturing the seme		300
			•		US	6660611	20031299	Ë	Method to form a corrugated structure for enhanced departance with	438/396	257/521.03
			•		2.4			<u>.</u>	plurality of boro-phospho silicate class including desmanium		
118	£.:	f.:	$\mathbf{r}$	$\mathbf{r}$	US	6656748	20031202	38	FeRMM capacitor post stack etch clean/repair	438/3	257/E21.00
		: .			E &		awamaw	2.5		ianaran na na na	2637631.3
	5	r.	٣	~	95	6635498	20031021		Method of patterning a FeRRH capacitor with a sidewall during bottom	438/3	257/221.00
4 ( 0.000 0.000 0.000 0.000					* /		565533333		electrone etch infrared detecting element, infrared two-dimensional image sensor, and	038/3	250/338.2
	7:	r	1	<b>.</b>	(13)	6635495	20031921		method of manufacturing the same		438/54
3.1	• • • • •				84. US	6817205	20030909	67	Semiconductor storage device and process for mamufacturing the same	. <b> </b>	438/24:
	€.	<b>1</b>	1	£.,	P.1	001.700		,	The state of the s		438/2537
112			سر	,	US	6599840	20030729	84	Material removal method for forming a structure		257/E21.0
200000000		•	: <b>:</b>		BZ				· ·	ð	<b>.</b>
13	7	r	٦,	<b>,-</b> -:	បទ	6596648	20630722	6.3	Material removal method for forming a structure	338/748	257/521.00
											•
7	io.	/s: }	(83)	397							
	*****	· · · · · · · · ·			****				,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		